

Description

650V N-CHANNEL ENHANCEMENT MODE POWER MOSFET

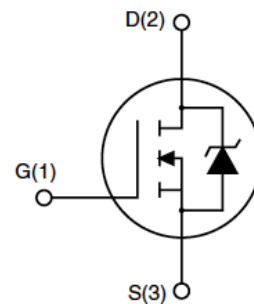
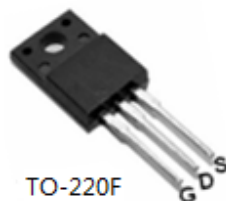
Features

- | | | |
|----------|-----------------------------|-------|
| V_{DS} | $R_{DS(ON)}$
@ 10V (typ) | I_D |
| 650V | 0.72Ω | 10A |
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS Compliant

Application

- Active power factor correction
- Uninterruptible Power Supply (UPS)
- Electronic lamp ballasts

Package



Ordering Information

Part Number	Marking	Case	Packaging
G10N65T	G10N65	TO-220	50pcs/Tube
G10N65F	G10N65	TO-220F	50pcs/Tube

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter		TO-220	TO-220F	Units
V _{DSS}	Drain-Source Voltage		650		V
V _{GSS}	Gate-Source Voltage		± 30		V
I _D	Continuous Drain Current	T _C = 25°C	10	10*	A
		T _C = 100°C	6.23	6.23*	A
I _{DM}	Pulsed Drain Current ^{note1}		40	40*	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}		280		mJ
dv/dt	Peak Diode Recovery Energy ^{note3}		4.5		V/ns
P _D	Power Dissipation	T _C = 25°C	156	50	W
	Linear Derating Factor	T _C > 25°C	1.25	0.4	W/°C
R _{θJC}	Thermal Resistance, Junction to Case		0.8	2.5	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C

*Drain current limited by maximum junction temperature

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	650	-	-	V
ΔV _{(BR)DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D = 250μA	-	0.68	-	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650V, V _{GS} = 0V	-	-	1	μA
		V _{DS} = 520V, T _C = 125°C	-	-	10	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} = 0V, V _{GS} = ±30V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage ^{note4}	V _{DS} = V _{GS} , I _D = 250μA	2	-	4	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D = 5A	-	0.72	0.85	Ω
g _{FS}	Forward Transconductance	V _{DS} =30V, I _D = 5A	-	5	-	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	1595	-	pF
C _{oss}	Output Capacitance		-	146.5	-	pF
C _{rss}	Reverse Transfer Capacitance		-	6.83	-	pF
Q _g	Total Gate Charge	V _{DD} = 520V, I _D = 10A, V _{GS} = 10V	-	38.7	-	nC
Q _{gs}	Gate-Source Charge		-	7.21	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	13.82	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 325V, I _D = 10A, RG = 10Ω, VGS = 10V	-	24.3	-	ns
t _r	Turn-On Rise Time		-	26.2	-	ns
t _{d(off)}	Turn-Off Delay Time		-	73.1	-	ns
t _f	Turn-Off Fall Time		-	33.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	10	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	40	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 10A	-	-	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _F = 10A,	-	611	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt =100A/μs	-	4.0	-	uC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 10\text{mH}$, $I_{AS} = 7.5A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. $I_{SD} \leq 10A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq B_{VDSS}$, Starting $T_J = 25^{\circ}\text{C}$
4. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

Typical Performance Characteristics

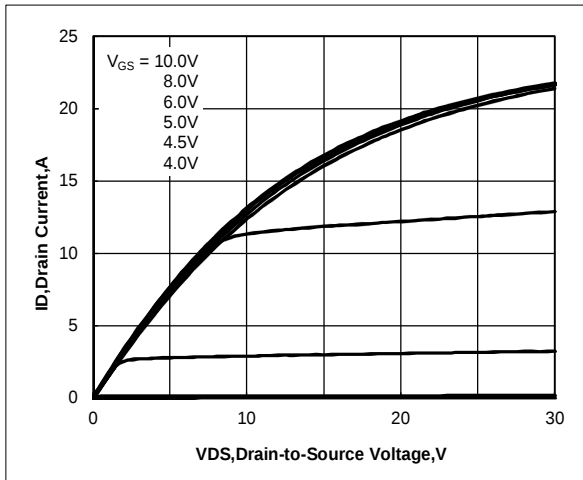


Figure 1. Output Characteristics

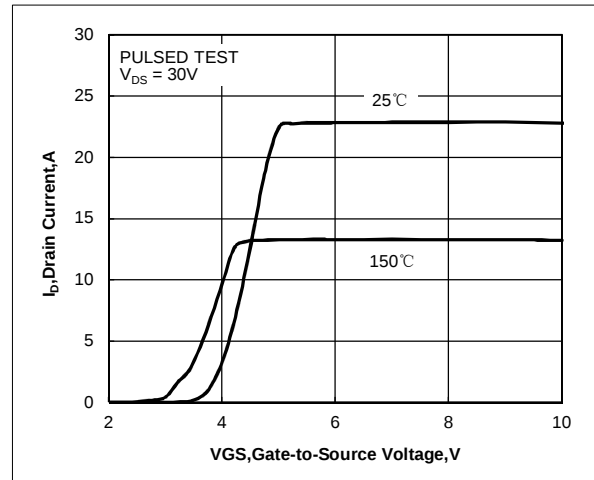


Figure 2. Transfer Characteristics

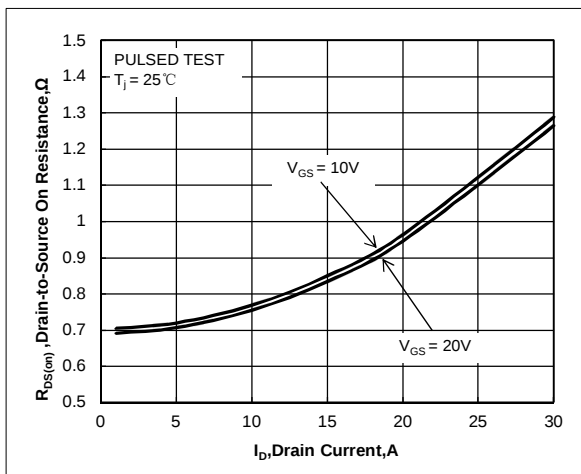


Figure 3. Drain-to-Source On Resistance vs. Drain Current and Gate Voltage

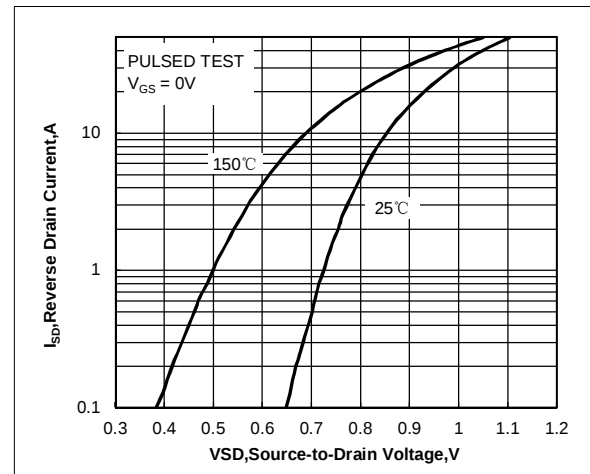


Figure 4. Body Diode Forward Voltage vs. Source Current and Temperature

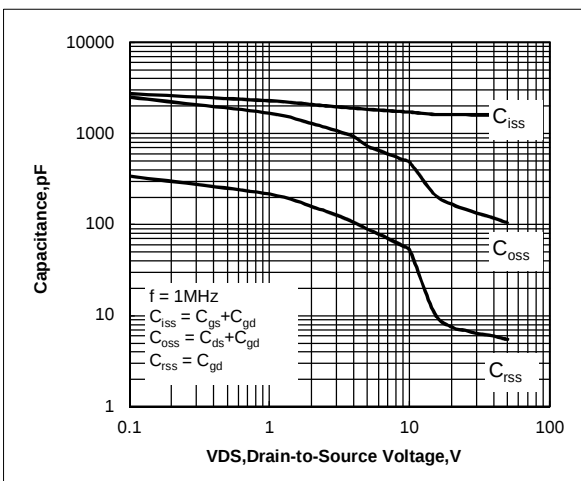


Figure 5. Capacitance Characteristics

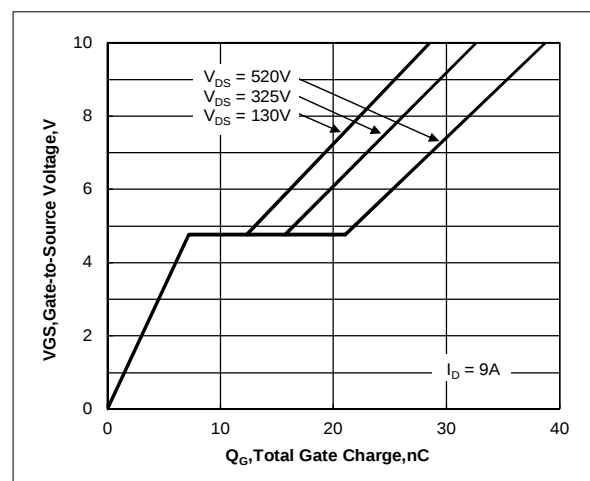


Figure 6. Gate Charge Characteristics

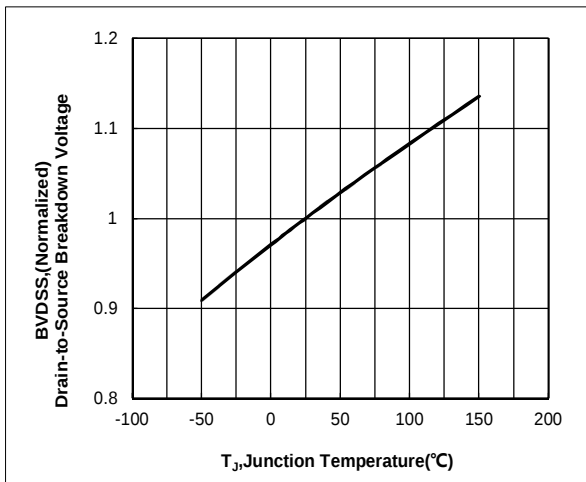


Figure 7. Normalized Breakdown Voltage vs. Junction Temperature

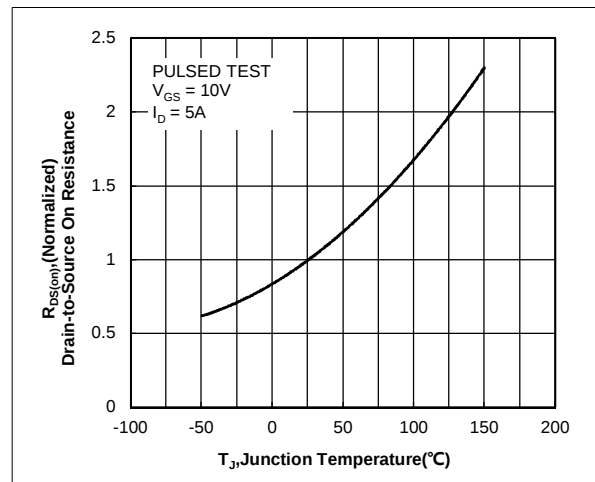


Figure 8. Normalized On Resistance vs. Junction Temperature

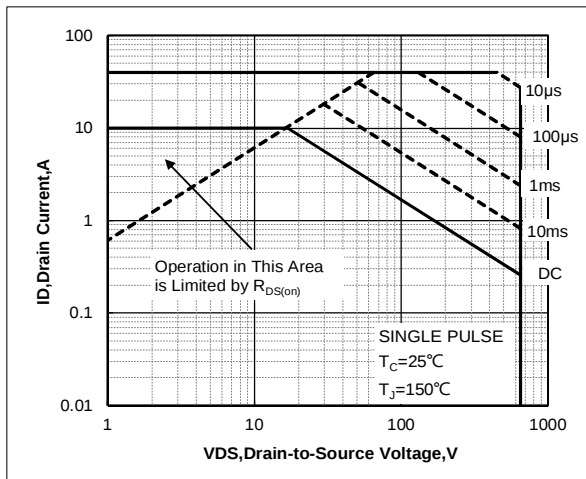


Figure 9. Maximum Safe Operating Area

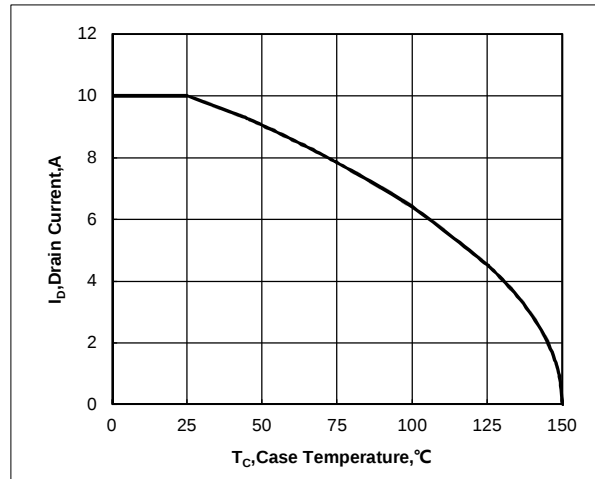


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

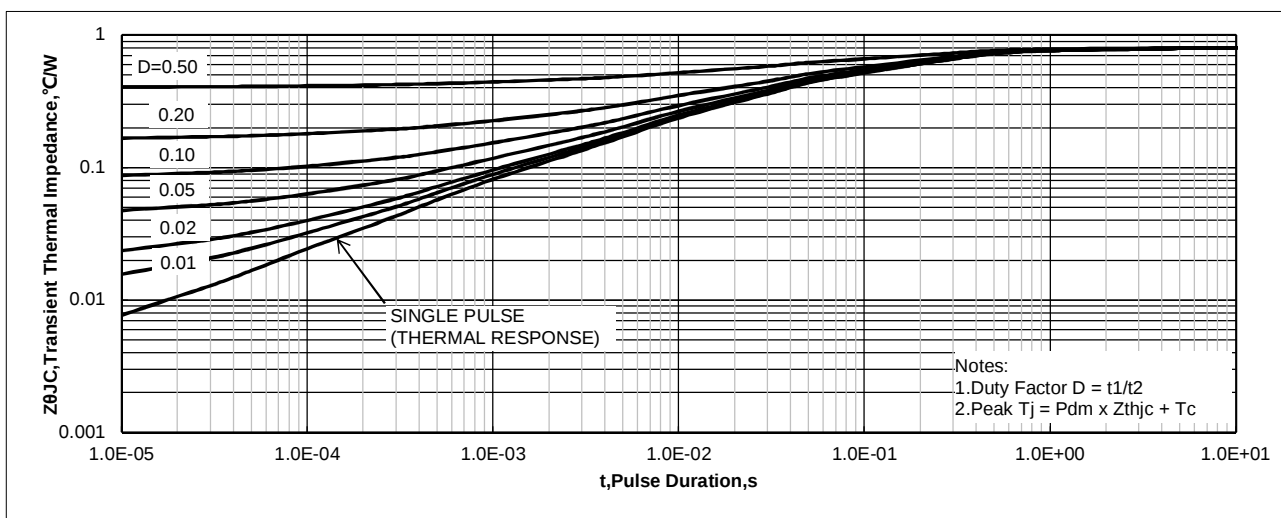


Figure 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

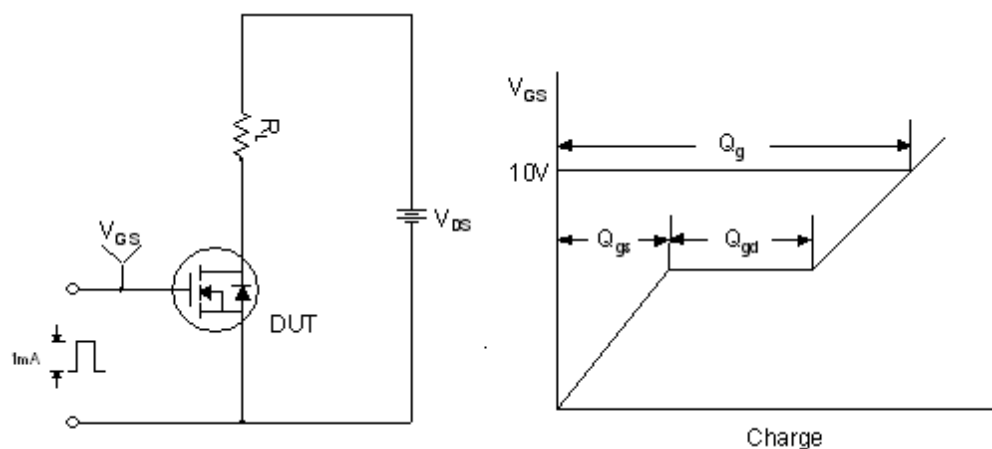


Figure 12. Gate Charge Test Circuit & Waveform

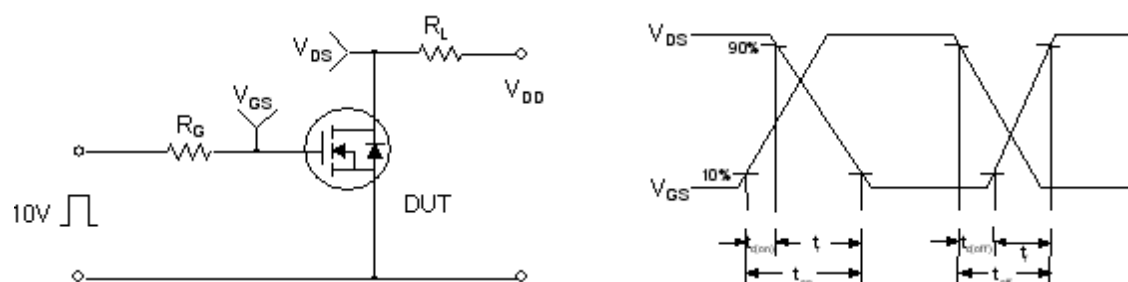


Figure 13. Resistive Switching Test Circuit & Waveforms

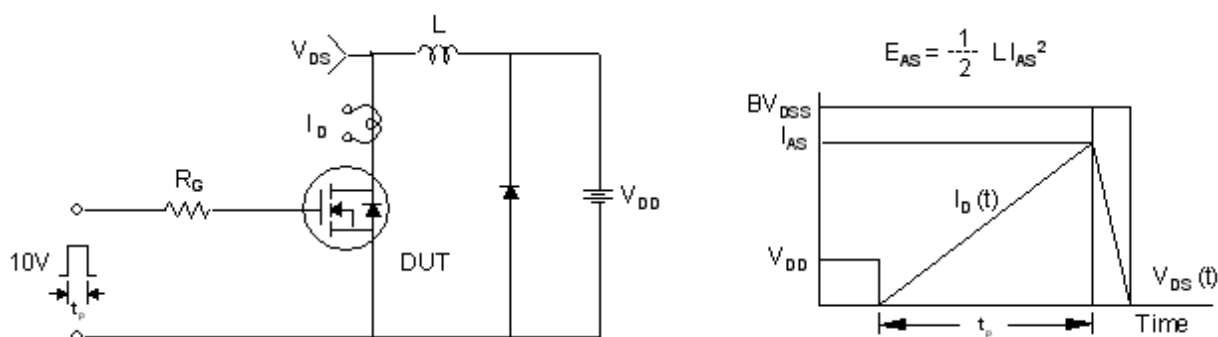


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

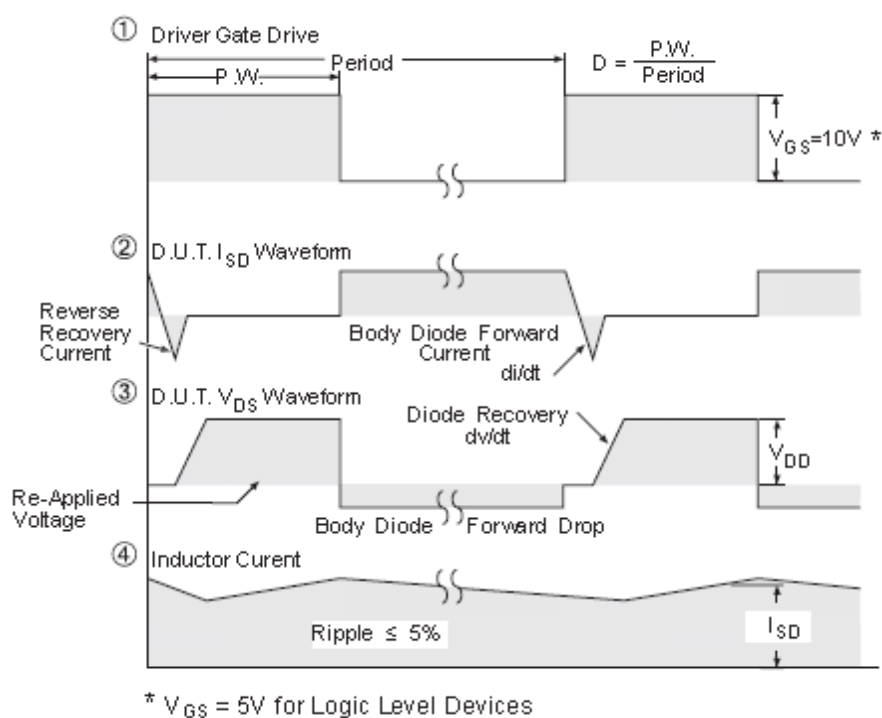
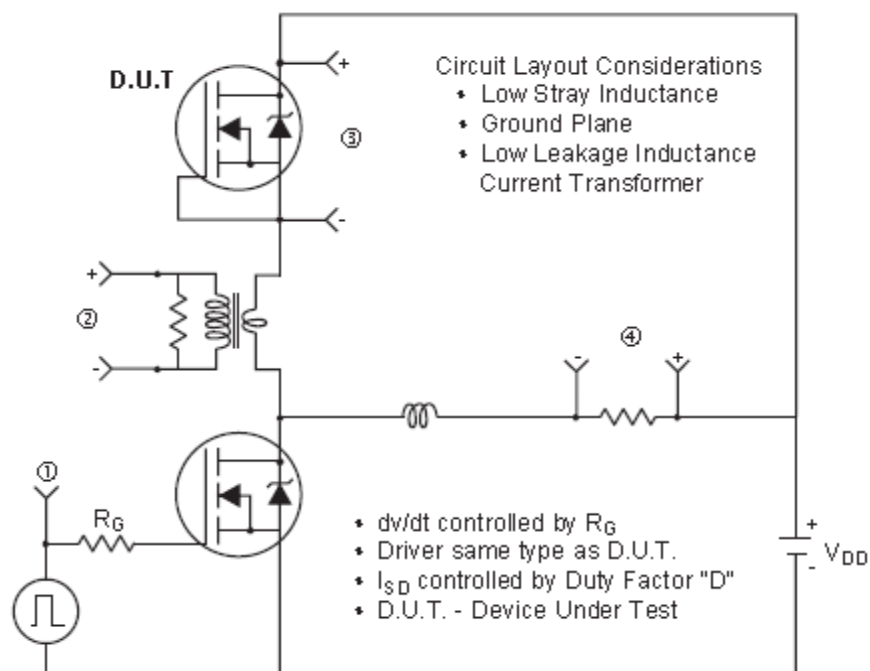
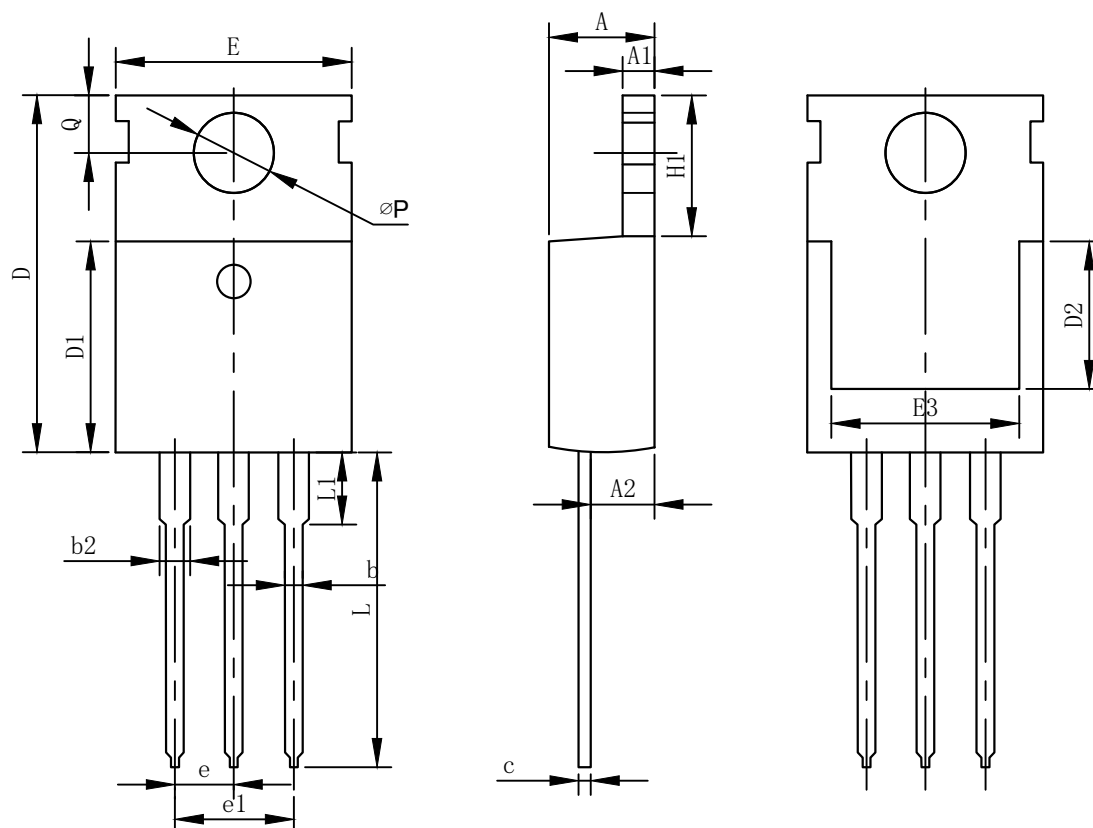


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

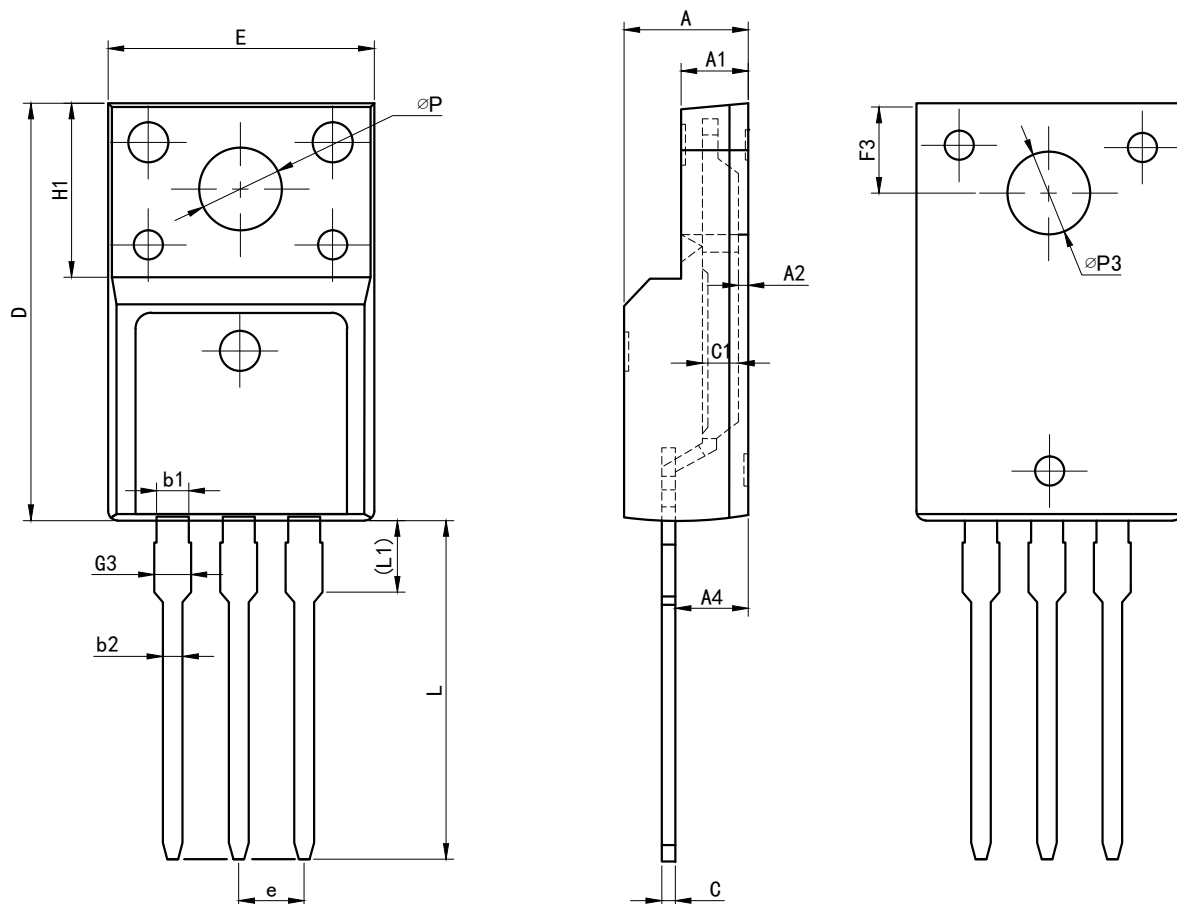
TO-220 Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	4.37	4.57	4.70
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.70	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	—	—
E	9.70	10.00	10.30
E3	7.00	—	—
e	2.54BSC		
e1	5.08BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	—	3.10	3.40
øP	3.40	3.60	3.80
Q	2.60	2.80	3.00

TO-220F Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.93	3.03	3.13
ϕP	3.03	3.18	3.38
$\phi P3$	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95